

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	176	(yewebdar or tadesse) and ("118"/\$.ccls. or "264"/\$.ccls.)	US-PGPUB; USPAT	OR	OFF	2004/12/01 11:54
S77	1792	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/01 12:01
S78	7	((("5,626,675") or ("5,213,650") or ("5,966,635"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/23 17:15
S79	0	chuck near5 reciev\$3 near7 backside near3 (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 10:38
S80	0	reciev\$3 near7 backside near3 (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 10:38
S81	11137	backside near3 (wafer or substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 10:54
S82	34	S77 and S81	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 10:54
S83	466	backside near3 (wafer or substrate) near7 vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 11:56
S84	136	S83 and rins\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 10:56

S85	122	S84 and pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 10:56
S86	4	S77 and S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 11:09
S87	139	backside near3 (wafer or substrate) near7 rins\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 15:23
S89	6	S87 and S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 11:29
S90	17	("5529626").URPN.	USPAT	OR	OFF	2004/11/23 16:39
S91	7	("4518078" "4685852" "5061144" "5238499" "5292554" "5315749" "5403397").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/23 11:22
S92	4	S90 and rins\$3 near5 back\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 11:23
S93	6	S87 and arms near7 lift\$3 near5 (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 11:29
S94	139	backside near3 (wafer or substrate) near7 rins\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 15:24
S95	213	(backside or (back near side)) near3 (wafer or substrate) near7 rins\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 15:24

S96	46	S95 and gas near7 source\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 15:46
S97	17	S95 and gas near7 source\$1 same vacuum same switch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 15:50
S98	1	S95 and gas near7 source\$1 same vacuum same switch\$3 and neutral near gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 15:50
S99	1	S95 and gas near7 source\$1 same vacuum near channel\$1 same switch\$3 and neutral near gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 16:02
S100	1792	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/23 16:01
S101	0	S100 and gas near7 source\$1 same vacuum near channel\$1 same switch\$3 and neutral near gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 16:03
S102	0	S100 and gas near7 source\$1 same vacuum near channel\$1 same switch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 16:03
S103	1	wafer same process\$3 near chamber and gas near7 source\$1 same vacuum near channel\$1 same switch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 16:04
S104	6	chamber\$1 and gas same vacuum near channel\$1 same switch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 16:06

S10 5	1	S100 and chamber\$1 same gas same vacuum same switch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 16:41
S10 6	18	"5529626"	USPAT	OR	OFF	2004/11/23 16:40
S10 7	2482	(118/50).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/23 16:41
S10 8	4	S107 and chamber\$1 same gas same vacuum same switch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 16:41
S10 9	2	("6033135").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/23 17:17
S11 0	259	(396/611).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/23 17:17
S11 1	4	("4590094" "4851263" "5650196" "5930549").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/11/23 17:19
S11 2	4	("6033135").URPN.	USPAT	OR	OFF	2004/11/23 17:19
S11 3	3	S112 and control\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/23 17:47
S11 5	855	(396/612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/24 08:07
S11 6	0	(396/697).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/28 11:48

S11 7	1	tapered near shelf\$1 same wafer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 08:44
S11 8	3332	tapered same wafer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 08:50
S11 9	1792	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/24 08:44
S12 0	0	("006and7").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/24 08:44
S12 1	16	S118 and S119	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 08:51
S12 2	1966	arms near5 wafer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 08:51
S12 3	39	S122 and S119	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:22
S12 4	466	backside near3 (wafer or substrate) near7 vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 11:59
S12 5	1314	wafer near5 diameter near7 "300"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:37

S12 6	8	S125 and S119	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:22
S12 7	8	wafer near5 diameter near7 "300" same contact near surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:52
S12 8	1	chuck near5 diameter near7 "300" same contact near surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:53
S12 9	2	chuck same diameter near7 "300" same contact near surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:54
S13 0	375	chuck same diameter same contact near surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 10:04
S13 1	16	chuck near7 diameter near7 contact near surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:55
S13 2	2	chuck same diameter same contact near surface same "280"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 09:58
S13 3	29	chuck same diameter same contact near surface same wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 10:26

S13 4	84	chuck same diameter same contact near surface same edge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 10:07
S13 9	472	(396/627).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/28 11:48
S14 0	2247	(134/902).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/28 11:49
S14 1	7	hiatt-mark\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/28 11:49
S14 2	100	mautz-karl\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/28 11:50
S14 3	7	schuster-ralf\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/28 11:51
S14 4	1793	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/29 08:47
S14 5	526	(118/313).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/29 10:48
S14 6	297	(118/62).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/29 11:06

S14 7	1400	(427/240).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/29 10:54
S14 8	9	S144 and S146	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/29 11:07
S14 9	5	S147 and S146	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/29 10:54
S15 0	1255	(118/63).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/11/29 11:06
S15 1	26	S144 and S150	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/29 11:07
S15 2	1630	(427/294).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/01 11:54
S15 3	1402	(427/240).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/01 11:55
S15 4	572	(427/425).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/01 11:55
S15 5	27	S152 and S153	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 11:56

S15 6	11	S152 and S154	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 11:56
S15 8	1796	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/01 12:02
S15 9	949	vacuum near3 (channels or passages or openings) same (gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 12:01
S16 1	3	S152 and S159	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 12:04
S16 2	0	S153 and S159	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 12:02
S16 3	0	S154 and S159	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 12:03
S16 4	1106	(396/611,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/01 12:03
S16 5	1	S164 and S159	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 12:04
S16 6	1	S158 and S159	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/01 12:04